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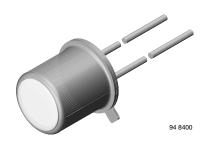




Vishay Semiconductors



Infrared Emitting Diode, RoHS Compliant, 950 nm, GaAs



DESCRIPTION

TSTS7500 is an infrared, 950 nm emitting diode in GaAs technology in a hermetically sealed TO-18 package with flat glass window.

FEATURES

Package type: leaded
Package form: TO-18
Dimensions (in mm): Ø 4.7
Peak wavelength: λ_p = 950 nm

High reliability

High radiant power

High radiant intensity

• Angle of half intensity: $\phi = \pm 30^{\circ}$

Low forward voltage

• Suitable for high pulse current operation

· Good spectral matching with Si photodetectors

 Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



· Radiation source in near infrared range

PRODUCT SUMMARY					
COMPONENT	I _e (mW/sr)	φ (deg)	λ _P (nm)	t _r (ns)	
TSTS7500	1.6	± 30	950	800	

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
TSTS7500	Bulk	MOQ: 1000 pcs, 1000 pcs/bulk	TO-18	

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V _R	5	V	
Forward current	T _{case} ≤ 25 °C	I _F	250	mA	
Peak forward current	$t_p/T = 0.5, t_p \le 100 \ \mu s, T_{case} \le 25 \ ^{\circ}C$	I _{FM}	500	mA	
Surge forward current	t _p ≤ 100 μs	I _{FSM}	2.5	Α	
Power dissipation		P _V	170	mW	
	T _{case} ≤ 25 °C	P _V	500	mW	
Junction temperature		Tj	100	°C	
Storage temperature range		T _{stg}	- 55 to + 100	°C	
Thermal resistance junction/ambient	leads not soldered	R_{thJA}	450	K/W	
Thermal resistance junction/case	leads not soldered	R _{thJC}	150	K/W	

Note

 T_{amb} = 25 °C, unless otherwise specified

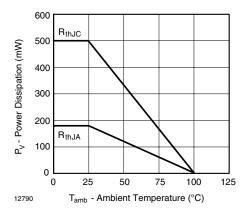




RoHS



Infrared Emitting Diode, RoHS Compliant, Vishay Semiconductors 950 nm, GaAs





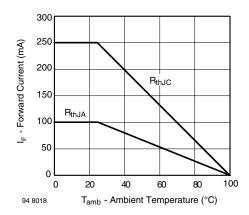


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100 \text{ mA}, t_p \le 20 \text{ ms}$	V_{F}		1.3	1.7	V
Temperature coefficient of V _F	I _F = 100 mA	TK _{VF}		- 1.3		mV/K
Breakdown voltage	I _R = 100 μA	$V_{(BR)}$	5			V
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0	C _j		30		pF
Radiant intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	l _e	1.25	1.6	8	mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p \le 20 \text{ ms}$	фe		7		mW
Temperature coefficient of φ _e	I _F = 100 mA	TΚφ _e		- 0.8		%/K
Angle of half intensity		φ		± 30		deg
Peak wavelength	I _F = 100 mA	λ_{p}		950		nm
Spectral bandwidth	I _F = 100 mA	Δλ		50		nm
Rise time	I _F = 100 mA	t _r		800		ns
	$I_F = 1.5 \text{ A}, t_p/T = 0.01, t_p \le 10 \mu\text{s}$	t _r		400		ns
Virtual source diameter		d		0.5		mm

Note

T_{amb} = 25 °C, unless otherwise specified

BASIC CHARACTERISTICS

 T_{amb} = 25 °C, unless otherwise specified

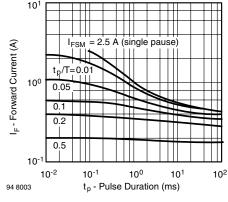


Fig. 3 - Pulse Forward Current vs. Pulse Duration

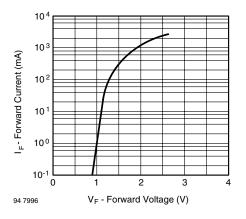


Fig. 4 - Forward Current vs. Forward Voltage

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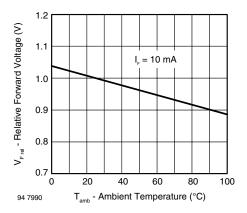


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

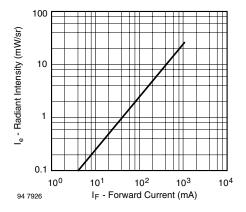


Fig. 6 - Radiant Intensity vs. Forward Current

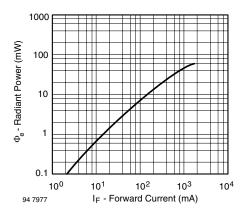


Fig. 7 - Radiant Power vs. Forward Current

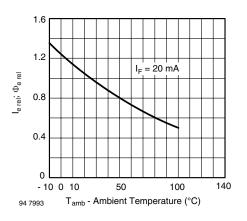


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

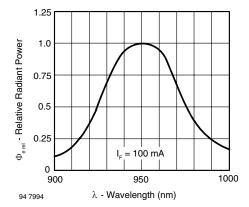


Fig. 9 - Relative Radiant Power vs. Wavelength

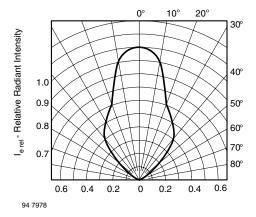
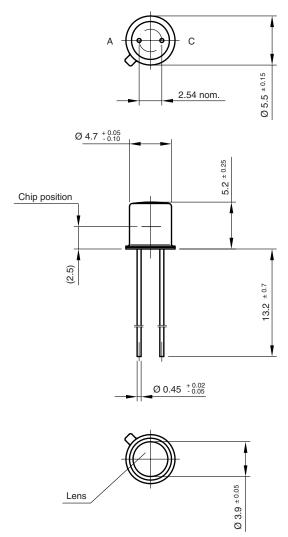


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement



Infrared Emitting Diode, RoHS Compliant, Vishay Semiconductors 950 nm, GaAs

PACKAGE DIMENSIONS in millimeters





technical drawings according to DIN specifications

Drawing-No.: 6.503-5001.02-4

Issue: 1; 24.08.98

14485



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